

S1954

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

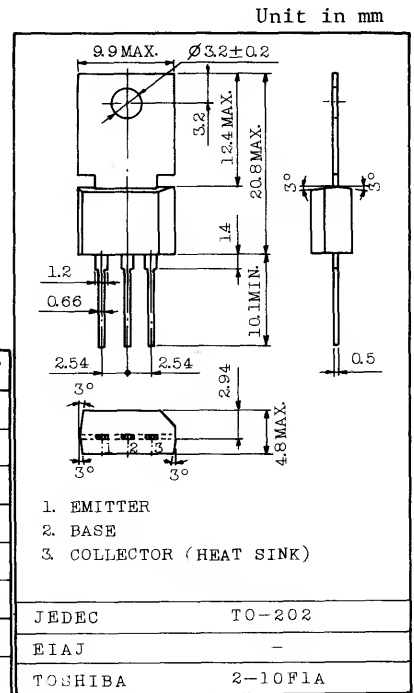
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- . Suitable for TV Sound Output, Vert. Deflection Output.
- . Designed for Complementary Use with S1955.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	50	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	1.5	A
Emitter Current	I _E	-1.5	A
Collector Power Dissipation	P _C	1.5	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



Weight : 1.4g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =50V, I _E =0	-	-	1.0	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} =5V, I _C =0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CE0}	I _C =10mA, I _B =0	50	-	-	V
DC Current Gain	h _{FE}	V _{CE} =2V, I _C =150mA	70	-	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A, I _B =0.1A	-	-	1.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} =10V, I _C =10mA	0.50	0.60	0.70	V
Transition Frequency	f _T	V _{CE} =10V, I _C =100mA	50	100	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	20	-	pF

